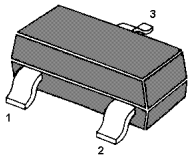
BCW30

PNP Silicon Epitaxial Planar Transistor

general purpose switching and amplification



1. Base 2. Emitter 3. Collector
TO-236 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	32	V
Collector Emitter Voltage	$-V_{CEO}$	32	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	100	mA
Peak Collector Current	$-I_{CM}$	200	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE}$ = 5 V, $-I_C$ = 2 mA	h_{FE}	215	-	500	-
Collector Base Cutoff Current at $-V_{CB}$ = 30 V	$-I_{CBO}$	-	-	100	nA
Emitter Base Cutoff Current at $-V_{EB}$ = 5 V	$-I_{EBO}$	-	-	100	nA
Collector Base Breakdown Voltage at $-I_C$ = 10 µA	$-V_{(BR)CBO}$	32	-	-	V
Collector Emitter Breakdown Voltage at $-I_C$ = 1 mA	$-V_{(BR)CEO}$	32	-	-	V
Emitter Base Breakdown Voltage at $-I_E$ = 10 µA	$-V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $-I_C$ = 10 mA, $-I_B$ = 0.5 mA	$-V_{CE(sat)}$	-	-	0.3	V
Base Emitter Voltage at $-V_{CE}$ = 5 V, $-I_C$ = 2 mA	$-V_{BE(on)}$	0.6	-	0.75	V
Transition Frequency at $-V_{CE}$ = 5 V, I_E = 10 mA, f = 100 MHz	f_T	100	-	-	MHz
Collector Base Capacitance at $-V_{CB}$ = 10 V, f = 1 MHz	C_{ob}	-	4.5	-	pF

Dated : 24/08/2007